

ABSTRACT OF THE DISCLOSURE

A TFT having a high threshold voltage is connected to the source electrode of each TFT that constitutes a CMOS circuit. In another aspect, pixel thin-film transistors are constructed such that a thin-film transistor more distant from a gate line drive circuit has a lower threshold voltage. In a further aspect, a control film that is removable in a later step is formed on the surface of the channel forming region of a TFT, and doping is performed from above the control film.

09451663-113099